



# PSMN0R9-30ULD

N-channel 30 V, 0.87 mΩ, 300 A logic level MOSFET in SOT1023A enhanced package for UL2595, using NextPowerS3 Schottky-Plus Technology

23 May 2018

Product data sheet

## 1. General description

SOT1023A with improved creepage and clearance to meet UL2595 requirements. 300 Amp logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

## 2. Features and benefits

- Improved creepage and clearance – meets the requirements of UL2595
- 300 A capability
- Avalanche rated, 100% tested at  $I_{AS} = 190$  A
- Ultra low  $Q_G$ ,  $Q_{GD}$  and  $Q_{OSS}$  for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1  $\mu$ A leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 150 °C
- Wave solderable; exposed leads for optimal visual solder inspection

## 3. Applications

- Brushed and brushless motor control
- Battery powered appliances where enhanced creepage and clearance is required to meet UL2595
- For non-UL2595 applications please use PSMN0R9-30YLD

## 4. Quick reference data

Table 1. Quick reference data

| Symbol    | Parameter               | Conditions  |     | Min | Typ | Max | Unit |
|-----------|-------------------------|---|-----|-----|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $25\text{ °C} \leq T_j \leq 150\text{ °C}$                                |     | -   | -   | 30  | V    |
| $I_D$     | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a> | [1] | -   | -   | 300 | A    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                          |     | -   | -   | 227 | W    |
| $T_j$     | junction temperature    |   |     | -55 | -   | 150 | °C   |

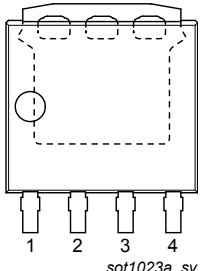
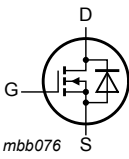
N-channel 30 V, 0.87 mΩ, 300 A logic level MOSFET in SOT1023A enhanced package for UL2595, using NextPowerS3 Schottky-Plus Technology

| Symbol                         | Parameter                        | Conditions  | Min | Typ  | Max  | Unit |
|--------------------------------|----------------------------------|---|-----|------|------|------|
| <b>Static characteristics</b>  |                                  |   |     |      |      |      |
| R <sub>DS(on)</sub>            | drain-source on-state resistance | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>                           | -   | 0.79 | 1.09 | mΩ   |
|                                |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>                            | -   | 0.65 | 0.87 | mΩ   |
| <b>Dynamic characteristics</b> |                                  |   |     |      |      |      |
| Q <sub>GD</sub>                | gate-drain charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a> | -   | 13.5 | -    | nC   |
| Q <sub>G(tot)</sub>            | total gate charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>  | -   | 109  | -    | nC   |
| <b>Source-drain diode</b>      |                                  |   |     |      |      |      |
| S                              | softness factor                  | I <sub>S</sub> = 25 A; di/dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V; <a href="#">Fig. 16</a>          | -   | 0.9  | -    |      |

[1] 300A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline  | Graphic symbol  |
|-----|--------|-----------------------------------|---|---|
| 1   | S      | source                            |  <p>LFAK56-UL2595<br/>(SOT1023A)</p> |  <p>mbb076</p> |
| 2   | S      | source                            |   |   |
| 3   | S      | source                            |   |   |
| 4   | G      | gate                              |   |   |
| mb  | D      | mounting base; connected to drain |   |   |

## 6. Ordering information

Table 3. Ordering information

| Type number   | Package       |  |          |
|---------------|---------------|--|----------|
|               | Name          | Description  | Version  |
| PSMN0R9-30ULD | LFAK56-UL2595 | plastic, single-ended surface-mounted package (LFAK56); 4 leads; 1.27 mm pitch | SOT1023A |

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## 7. Marking

Table 4. Marking codes

| Type number   | Marking code |
|---------------|--------------|
| PSMN0R9-30ULD | 0D93UL       |

## 8. Limiting values

Table 5. Limiting values

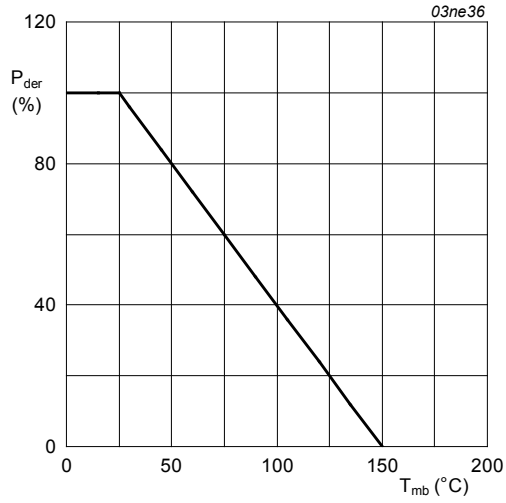
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                                    | Conditions  |     | Min | Max  | Unit |
|-----------------------------|--|---|-----|-----|------|------|
| $V_{DS}$                    | drain-source voltage                         | $25\text{ °C} \leq T_j \leq 150\text{ °C}$  |     | -   | 30   | V    |
| $V_{DGR}$                   | drain-gate voltage                           | $25\text{ °C} \leq T_j \leq 150\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$   |     | -   | 30   | V    |
| $V_{GS}$                    | gate-source voltage                          |   |     | -20 | 20   | V    |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>  |     | -   | 227  | W    |
| $I_D$                       | drain current                                | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>   | [1] | -   | 300  | A    |
|                             |  | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 2</a>  |     | -   | 284  | A    |
| $I_{DM}$                    | peak drain current                           | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a>   |     | -   | 1592 | A    |
| $T_{stg}$                   | storage temperature                          |   |     | -55 | 150  | °C   |
| $T_j$                       | junction temperature                         |   |     | -55 | 150  | °C   |
| $T_{sld(M)}$                | peak soldering temperature                   |   |     | -   | 260  | °C   |
| $V_{ESD}$                   | electrostatic discharge voltage              | HBM   |     | 2   | -    | kV   |
| <b>Source-drain diode</b>   |  |   |     |     |      |      |
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$   |     | -   | 242  | A    |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$  |     | -   | 1800 | A    |
| <b>Avalanche ruggedness</b> |  |   |     |     |      |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 25\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped; $t_p = 6.1\text{ ms}$ | [2] | -   | 2575 | mJ   |
| $I_{AS}$                    | non-repetitive avalanche current             | $V_{sup} \leq 30\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $R_{GS} = 50\text{ }\Omega$  | [2] | -   | 190  | A    |

[1] 300A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

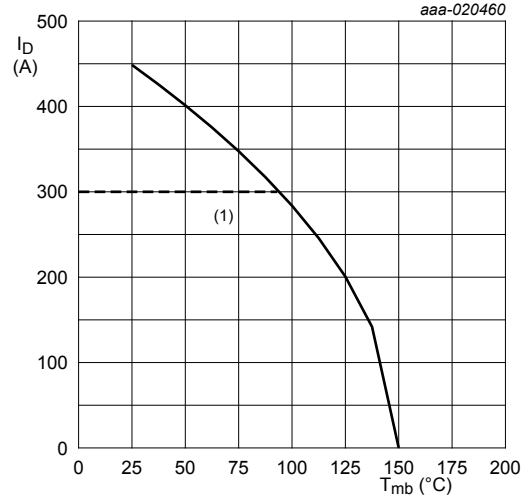
[2] Protected by 100% test

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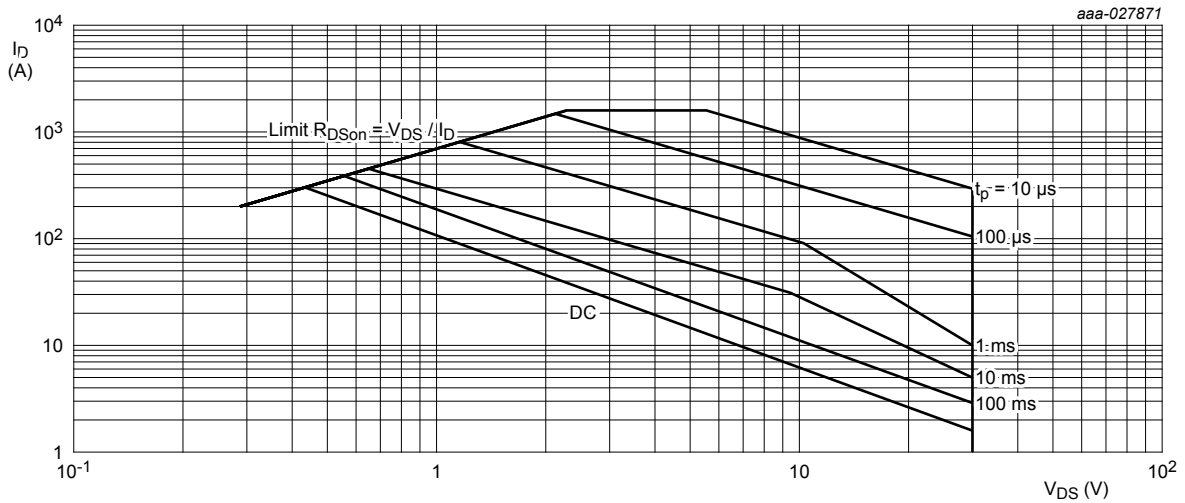
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

Fig. 1. Normalized total power dissipation as a function of mounting base temperature



(1) 300A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature  
 $V_{GS} \geq 10V$

Fig. 2. Continuous drain current as a function of mounting base temperature



$T_{mb} = 25^{\circ}\text{C}$ ;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions             | Min | Typ  | Max  | Unit |
|----------------|---|------------------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | <a href="#">Fig. 4</a> | -   | 0.45 | 0.55 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | <a href="#">Fig. 5</a> | -   | 50   | -    | K/W  |
|                |   | <a href="#">Fig. 6</a> | -   | 125  | -    | K/W  |

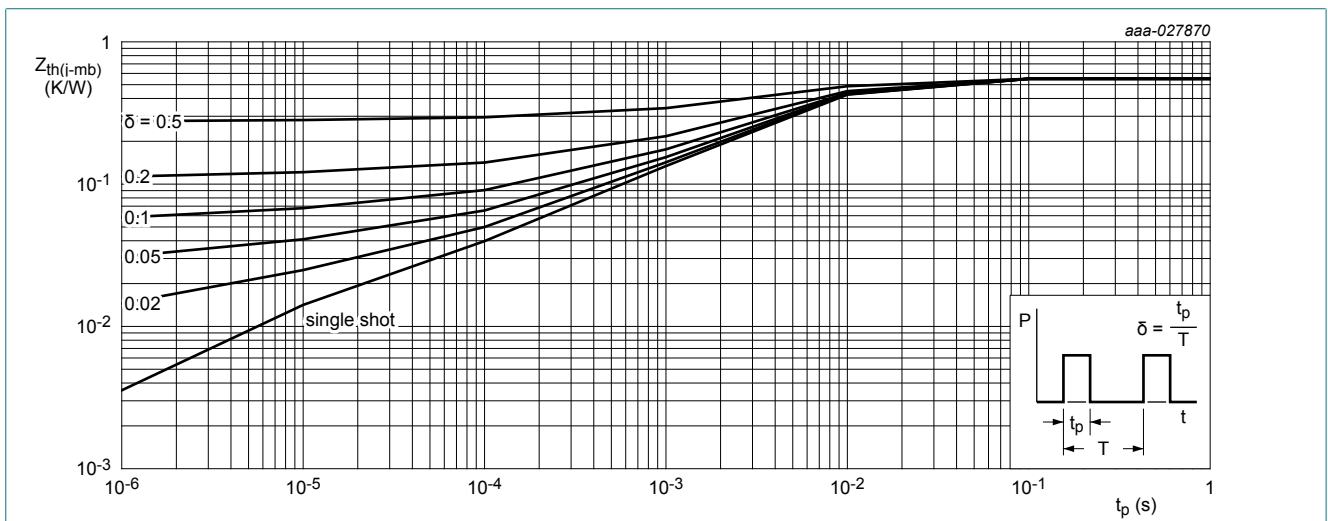


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

aaa-005750

aaa-005751

**Fig. 5.** PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

**Fig. 6.** PCB layout for thermal resistance junction to ambient minimum footprint; FR4 board; 2oz copper

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## 10. Characteristics

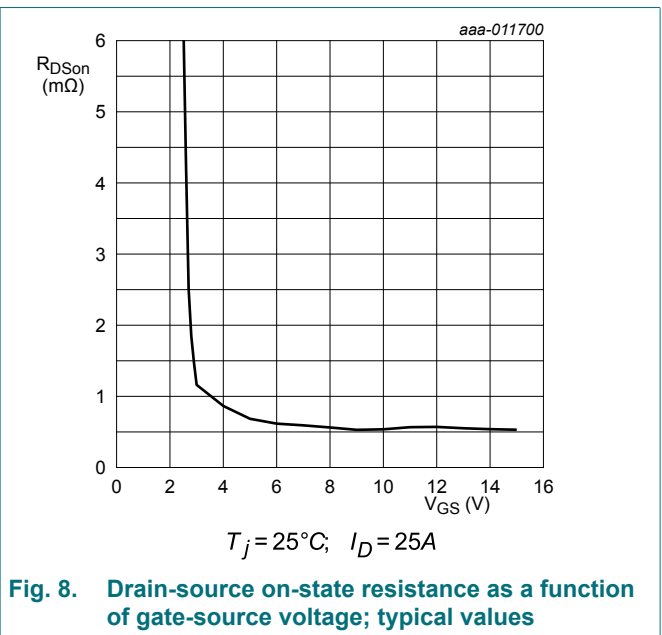
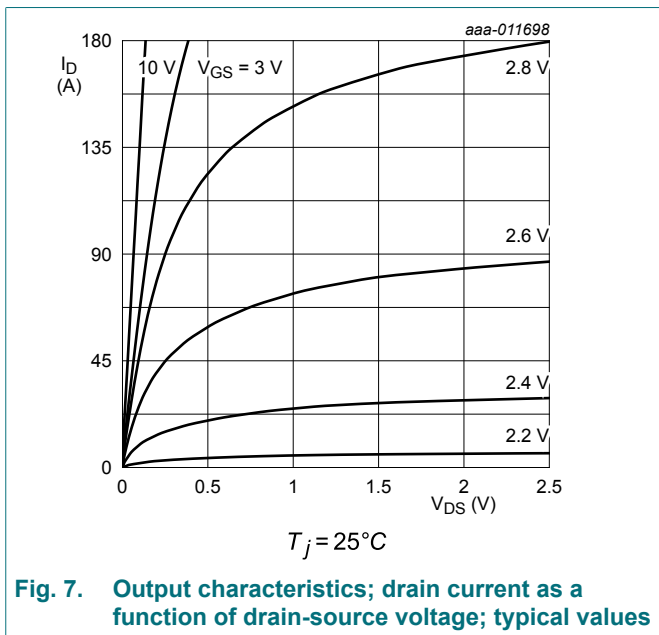
Table 7. Characteristics

| Symbol                         | Parameter  | Conditions  | Min | Typ  | Max  | Unit          |
|--------------------------------|--|---|-----|------|------|---------------|
| <b>Static characteristics</b>  |  |   |     |      |      |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage                           | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | 30  | -    | -    | V             |
|                                |  | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$   | 27  | -    | -    | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage                            | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C}$  | 1.2 | 1.5  | 2.2  | V             |
| $\Delta V_{GS(th)}/\Delta T$   | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ\text{C} \leq T_j \leq 150 \text{ }^\circ\text{C}$  | -   | -4.5 | -    | mV/K          |
| $I_{DSS}$                      | drain leakage current                                    | $V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | -   | -    | 1    | $\mu\text{A}$ |
|                                |  | $V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$   | -   | 3.7  | -    | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current                                     | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | -   | -    | 100  | nA            |
|                                |  | $V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$   | -   | -    | 100  | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance                         | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$<br><a href="#">Fig. 10</a>                       | -   | 0.79 | 1.09 | mΩ            |
|                                |  | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$<br><a href="#">Fig. 10; Fig. 11</a>             | -   | -    | 1.8  | mΩ            |
|                                |  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$<br><a href="#">Fig. 10</a>                        | -   | 0.65 | 0.87 | mΩ            |
|                                |  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$<br><a href="#">Fig. 10; Fig. 11</a>              | -   | -    | 1.44 | mΩ            |
| $R_G$                          | gate resistance  | $f = 1 \text{ MHz}$   | -   | 1.4  | -    | Ω             |
| <b>Dynamic characteristics</b> |  |   |     |      |      |               |
| $Q_{G(tot)}$                   | total gate charge  | $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$<br><a href="#">Fig. 12; Fig. 13</a>                         | -   | 109  | -    | nC            |
|                                |  | $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$<br><a href="#">Fig. 12; Fig. 13</a>                        | -   | 51   | -    | nC            |
|                                |  | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 0 \text{ V}$   | -   | 99   | -    | nC            |
| $Q_{GS}$                       | gate-source charge                                       | $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$<br><a href="#">Fig. 12; Fig. 13</a>                        | -   | 15.3 | -    | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge                         |   | -   | 10.5 | -    | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge                        |   | -   | 4.8  | -    | nC            |
| $Q_{GD}$                       | gate-drain charge  |   | -   | 13.5 | -    | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage                              | $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V};$ <a href="#">Fig. 12; Fig. 13</a>   | -   | 2.4  | -    | V             |
| $C_{iss}$                      | input capacitance  | $V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 14</a> | -   | 7668 | -    | pF            |
| $C_{oss}$                      | output capacitance                                       |   | -   | 2914 | -    | pF            |
| $C_{rss}$                      | reverse transfer capacitance                             |   | -   | 445  | -    | pF            |

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| Symbol                    | Parameter                  | Conditions  | Min | Typ   | Max  | Unit |    |
|---------------------------|----------------------------|---|-----|-------|------|------|----|
| $t_{d(on)}$               | turn-on delay time         | $V_{DS} = 15\text{ V}; R_L = 0.6\ \Omega; V_{GS} = 4.5\text{ V}; R_{G(ext)} = 5\ \Omega$                            | -   | 38.1  | -    | ns   |    |
| $t_r$                     | rise time                  |   | -   | 49.8  | -    | ns   |    |
| $t_{d(off)}$              | turn-off delay time        |   | -   | 63    | -    | ns   |    |
| $t_f$                     | fall time                  |   | -   | 42.6  | -    | ns   |    |
| $Q_{oss}$                 | output charge              | $V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}$                       | -   | 83.11 | -    | nC   |    |
| <b>Source-drain diode</b> |                            |   |     |       |      |      |    |
| $V_{SD}$                  | source-drain voltage       | $I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 15}$                            | -   | 0.76  | 1.2  | V    |    |
| $t_{rr}$                  | reverse recovery time      | $I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}; \text{Fig. 16}$ | -   | 52    | -    | ns   |    |
| $Q_r$                     | recovered charge           |   | [1] | -     | 67   | -    | nC |
| $t_a$                     | reverse recovery rise time |   | -   | -     | 27.4 | -    | ns |
| $t_b$                     | reverse recovery fall time |   | -   | -     | 24.7 | -    | ns |
| S                         | softness factor            |   | -   | -     | 0.9  | -    |    |

[1] includes capacitive recovery



N-channel 30 V, 0.87 mΩ, 300 A logic level MOSFET in SOT1023A enhanced package for UL2595, using NextPowerS3 Schottky-Plus Technology

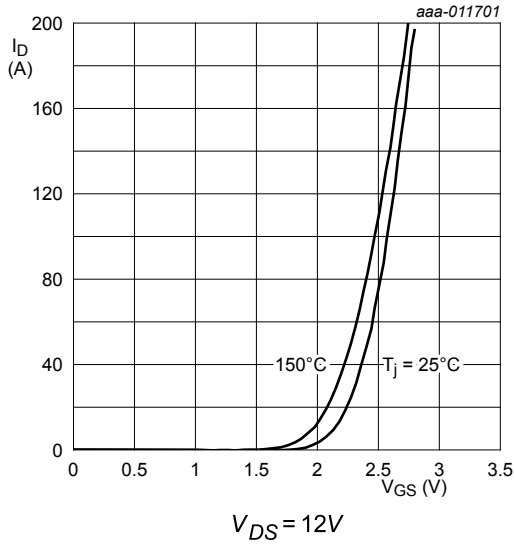


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

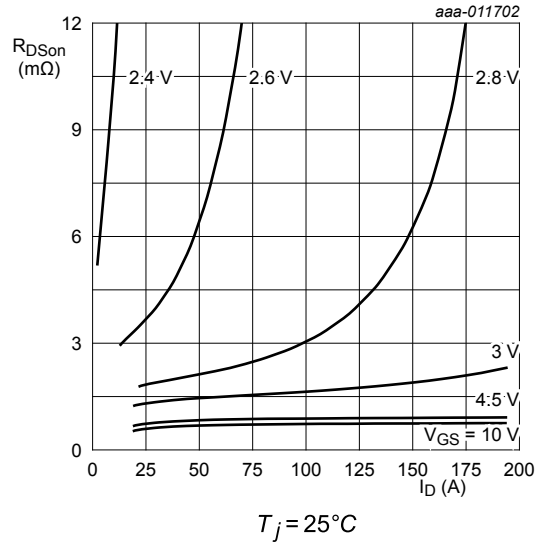


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

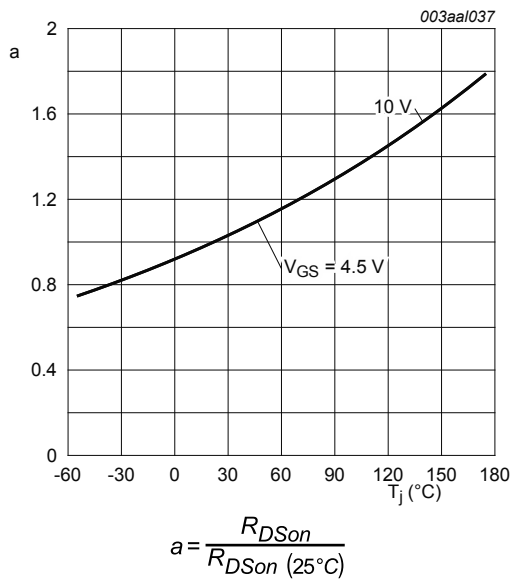


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

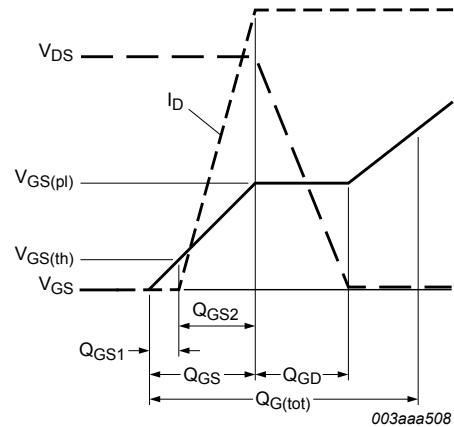


Fig. 12. Gate charge waveform definitions



N-channel 30 V, 0.87 mΩ, 300 A logic level MOSFET in SOT1023A enhanced package for UL2595, using NextPowerS3 Schottky-Plus Technology

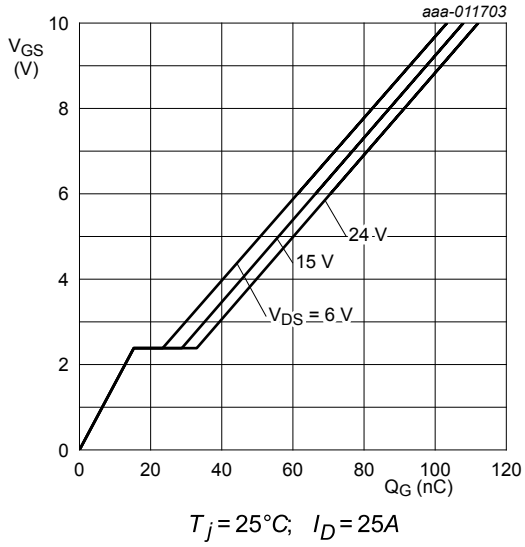


Fig. 13. Gate-source voltage as a function of gate charge; typical values

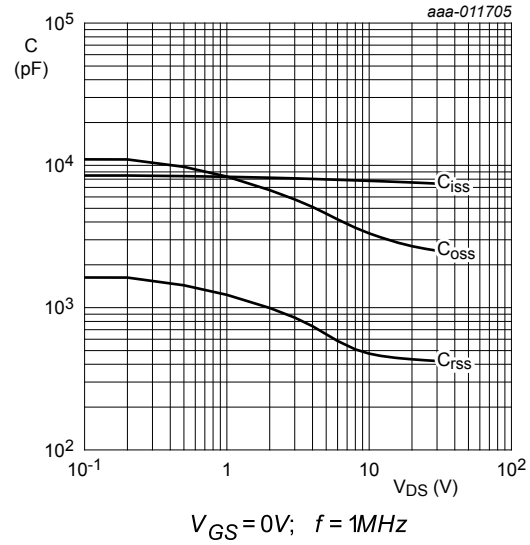


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

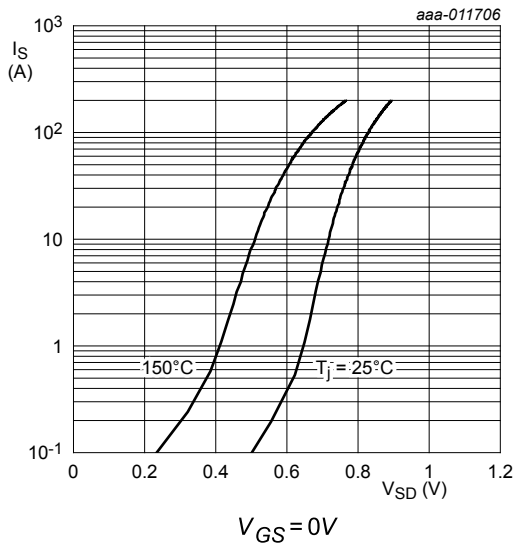


Fig. 15. Source current as a function of source-drain voltage; typical values

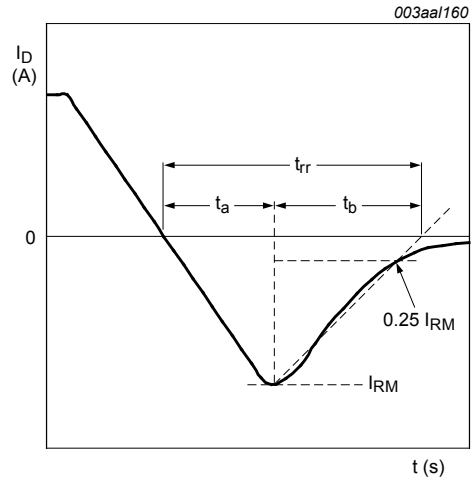


Fig. 16. Reverse recovery timing definition

N-channel 30 V, 0.87 mΩ, 300 A logic level MOSFET in SOT1023A enhanced package for UL2595, using NextPowerS3 Schottky-Plus Technology

### 11. Package outline

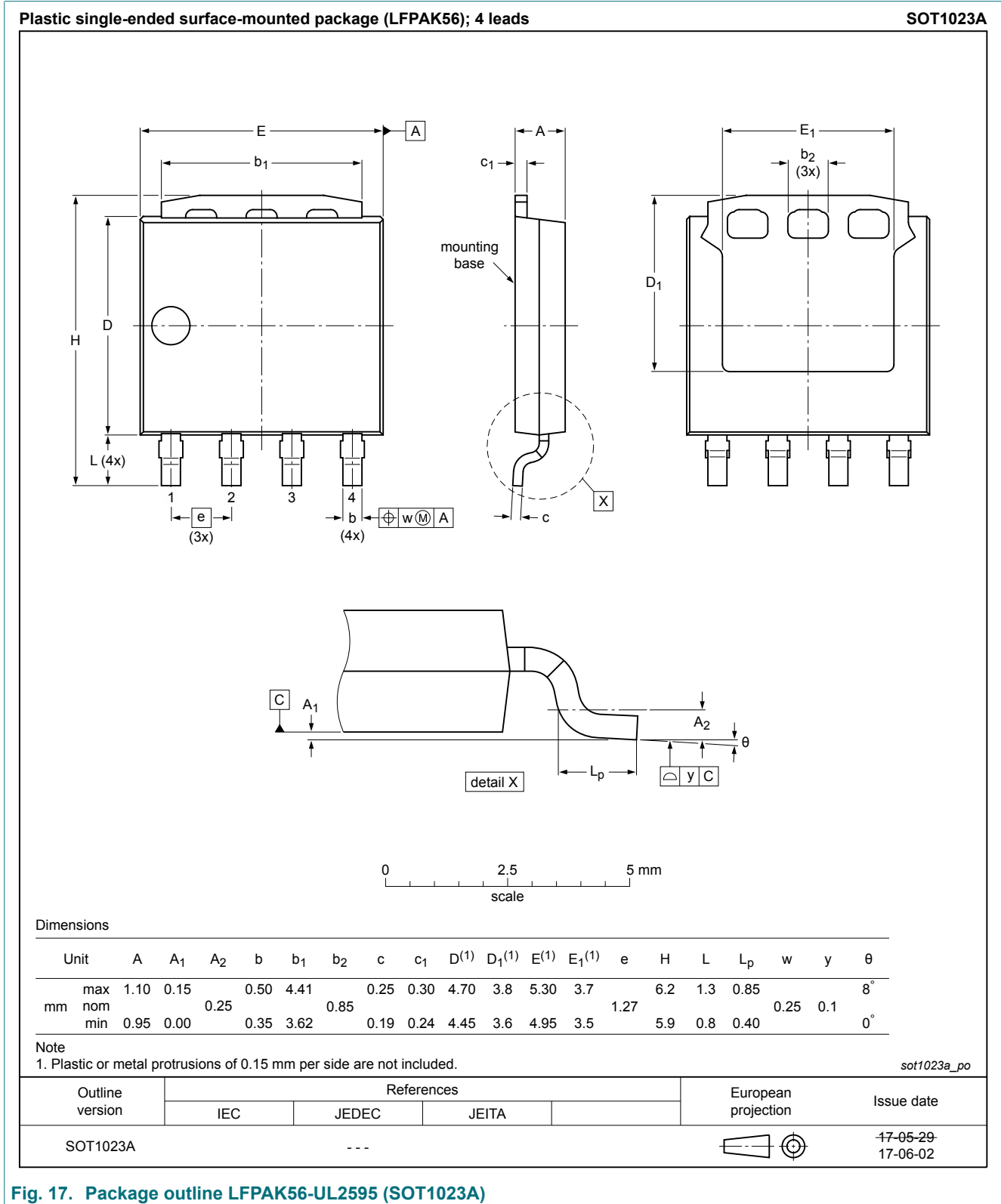


Fig. 17. Package outline LPAK56-UL2595 (SOT1023A)

## N-channel 30 V, 0.87 mΩ, 300 A logic level MOSFET in SOT1023A enhanced package for UL2595, using NextPowerS3 Schottky-Plus Technology

## 12. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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**N-channel 30 V, 0.87 mΩ, 300 A logic level MOSFET in SOT1023A enhanced package for UL2595, using NextPowerS3 Schottky-Plus Technology**

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N-channel 30 V, 0.87 m $\Omega$ , 300 A logic level MOSFET in SOT1023A enhanced package for UL2595, using NextPowerS3 Schottky-Plus Technology

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Date of release: 23 May 2018

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